

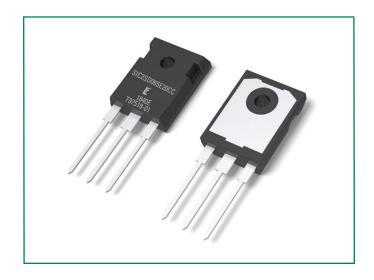
LSIC2SD065E20CCA 650 V, 20 A SiC Schottky Barrier Diode











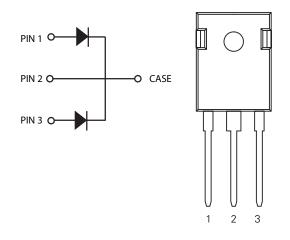
Description

This series of silicon carbide (SiC) Schottky diodes has negligible reverse recovery current, high surge capability, and a maximum operating junction temperature of 175 °C. This diode series is ideal for applications where improvements in efficiency, reliability, and thermal management are desired.

Features

- AEC-Q101 qualified
- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C. maximum operating junction temperature
- · Excellent surge capability
- Extremely fast, temperature-independent switching behavior
- Dramatically reduced switching losses compared to Si bipolar diodes

Circuit Diagram TO-247-3L



Applications

- · Boost diodes in PFC or DC/DC stages
- Switch-mode power supplies
- Uninterruptible power supplies
- Solar inverters
- Industrial motor drives
- EV charging stations

Environmental

- Littelfuse "RoHS" logo = RoHS RoHS conform
- Littelfuse "HF" logo = HF Halogen Free
- Littelfuse "Pb-free" logo = Pb Pb-free lead plating

Maximum Ratings

Characteristics	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	-	650	V
DC Blocking Voltage	V _R	T _J = 25 °C	650	V
Continuous Forward Current		T _C = 25 °C	27 / 54	_
(Per Leg/Component)	l _F	T _C = 147 °C	10 / 20	A
Non-Repetitive Forward Surge Current (Per Leg)	I _{FSM}	$T_{\rm C}$ = 25 °C, $t_{\rm p}$ = 10 ms, Half sine pulse	50	А
Power Dissipation	Б	T _c = 25 °C	100 / 200	W
(Per Leg/Component)	P _{Tot}	T _C = 110 °C	43 / 86	VV
Operating Junction Temperature	T	-	-55 to 175	°C
Storage Temperature	T _{STG}	-	-55 to 150	°C
Soldering Temperature	T _{sold}	-	260	°C



Electrical Characteristics (T₁ = 25 °C unless otherwise specified)

Characteristics Symbol			Value			
		Conditions	Min.	Тур.	Max.	Unit
Forward Voltage V _F	I _F = 10 A, T _J = 25 °C	-	1.5	1.8	V	
	V _F	I _F = 10 A, T _J = 175 °C	-	1.85	-	V
Reverse Current I _R	I _R	$V_R = 650 \text{ V}, T_J = 25 ^{\circ}\text{C}$	-	<1	50	μA
		$V_{R} = 650 \text{ V, T}_{J} = 175 ^{\circ}\text{C}$	-	25	-	μΑ
Total Capacitance C		$V_R = 1 V$, $f = 1 MHz$	-	470	-	
	С	V _R = 200 V, f = 1 MHz	-	60	-	pF
		V _R = 400 V, f = 1 MHz	-	43	-	
Total Capacitive Charge	Q _c	$V_R = 400 \text{ V}, Q_C = \int\limits_0^{V_R} C(V) dV$	-	30	-	nC

Thermal Characteristics

Characteristics	Symbol	Value	Unit
Thermal Resistance (Per Leg/Component)	R _{eJC}	1.50 / 0.75	°C/W

Figure 1: Typical Foward Characteristics

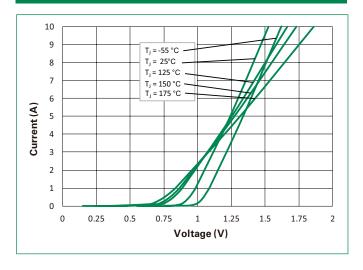


Figure 2: Typical Reverse Characteristics

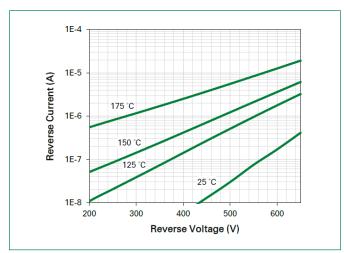




Figure 3: Power Derating

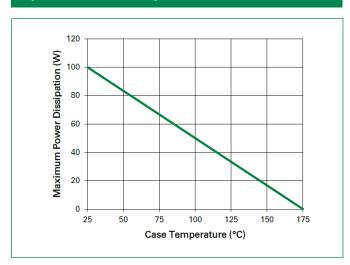


Figure 4: Current Derating

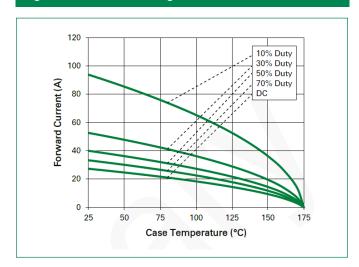


Figure 5: Capacitance vs. Reverse Voltage

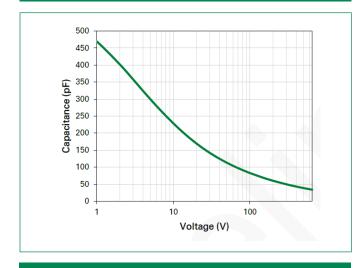


Figure 6: Capacitive Charge vs. Reverse Voltage

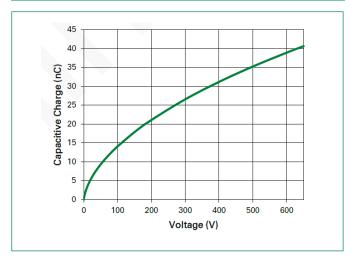


Figure 7: Stored Energy vs. Reverse Voltage

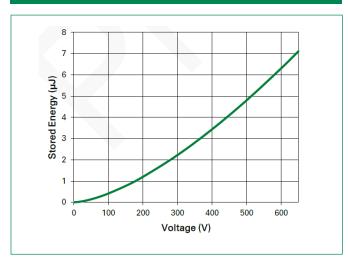
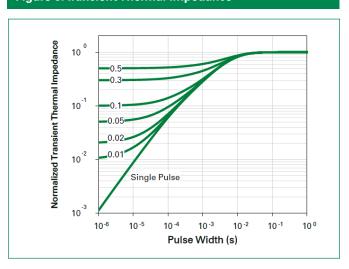
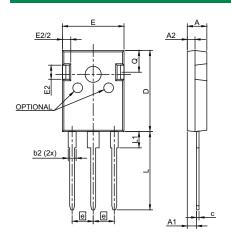


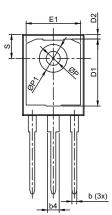
Figure 8: Transient Thermal Impedance



GEN2 SiC Schottky Diode LSIC2SD065E20CCA, 650 V, 20 A, TO-247-3L

Package Dimensions TO-247-3L





Recommended Hole Pattern Layout



Notes:

- Dimensions are in millimeters
- Dimension D, E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These measured at the outermost extreme of plastic body.

 3.øP to have a maximum draft angle of 1.5° to the top
- 3.øP to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 0.154"

Current el	Millimeters			
Symbol	Min	Nom	Max	
А	4.80	5.03	5.20	
A1	2.25	2.38	2.54	
A2	1.85	1.98	2.11	
b	0.99	-	1.40	
b2	1.65	-	2.39	
b4	2.59	-	3.43	
С	0.38	0.64	0.89	
D	20.80	20.96	21.34	
D1	13.50	-	-	
D2	0.51	1.19	1.35	
е	5.44 BSC			
Е	15.75	15.90	16.13	
E1	13.06	14.02	14.15	
E2	4.19	4.32	4.83	
L	19.81	20.19	20.57	
L1	3.81	4.19	4.45	
øΡ	3.55	3.61	3.66	
øP1	7.06	7.19	7.32	
Q	5.49	5.61	6.20	
S	6.05	6.17	6.30	

Part Numbering and Marking System



SIC	= SiC
2	= Gen2

SD = Schottky Diode 065 = Voltage Rating (650 V)

E = TO-247-3L

20 = Current Rating (20 A) CC = Common Cathode

Y = Year

Y = Year

WW = Week

X = Special Code

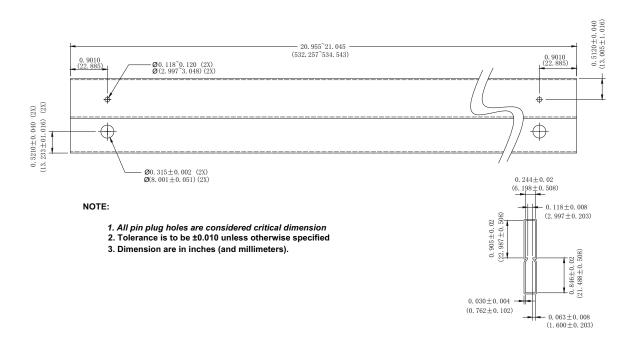
ZZZZZZ-ZZ = Lot Number

Packing Options

Part Number	Marking	Packing Mode	M.O.Q
LSIC2SD065E20CCA	SIC2SD065E20CC	Tube (30pcs)	450

GEN2 SiC Schottky Diode LSIC2SD065E20CCA, 650 V, 20 A, TO-247-3L

Packing Specification TO-247-3L



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